

ABSTRACT

1 A method for detecting the endpoint of a chemical mechanical polishing (CMP)
2 process uses the slope variation of temperature difference of polishing pad. The method
3 combines temperature measurement at polishing pad and atmosphere, and numerical
4 analysis to figure out the curve of temperature difference variation versus polishing time.
5 The endpoint of CMP is determined by the change of the slope of the curve. The method
6 allows endpoint to be detected in-situ at the polishing apparatus, without stopping
7 polishing process.